

3.3V-5V 1 Mbit (128Kb x 8) TIMEKEEPER $^{\mathbb{R}}$ SRAM

DATA BRIEFING

- INTEGRATED ULTRA LOW POWER SRAM, REAL TIME CLOCK, POWER-FAIL CONTROL CIRCUIT, BATTERY, AND CRYSTAL
- BCD CODED YEAR, MONTH, DAY, DATE, HOURS, MINUTES, and SECONDS
- AUTOMATIC POWER-FAIL CHIP DESELECT and WRITE PROTECTION
- WRITE PROTECT VOLTAGES (V_{PFD} = Power-fail Deselect Voltage):
 - $M48T128Y: 4.1V \le V_{PFD} \le 4.5V$
 - M48T128V: $2.7V \le V_{PFD} \le 3.0V$
- CONVENTIONAL SRAM OPERATION; UNLIMITED WRITE CYCLES
- SOFTWARE CONTROLLED CLOCK CALIBRATION for HIGH ACCURACY APPLICATIONS
- 10 YEARS of DATA RETENTION and CLOCK OPERATION in the ABSENCE of POWER
- PIN and FUNCTION COMPATIBLE with JEDEC STANDARD 128K X 8 SRAMS
- SELF-CONTAINED BATTERY and CRYSTAL in DIP PACKAGE

DESCRIPTION

The M48T128Y/V TIMEKEEPER RAM is a 128K x 8 non-volatile static RAM and real time clock. The special DIP package provides a fully integrated battery back-up memory and real time clock solution. The M48T128Y/V idirectly replaces industry standard 128K x 8 SRAM.

It also provides the non-volatility of Flash without any requirement for special write timing or limitations on the number of writes that can be performed. The 32 pin 600 mil DIP Hybrid houses a controller chip, SRAM, quartz crystal, and a long life lithium button cell in a single package.

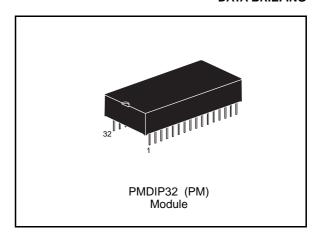
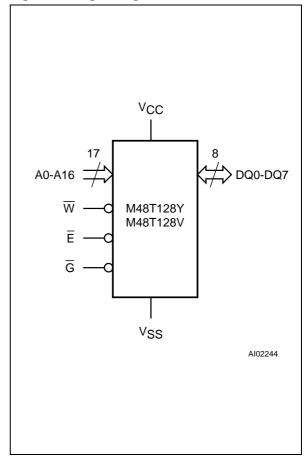
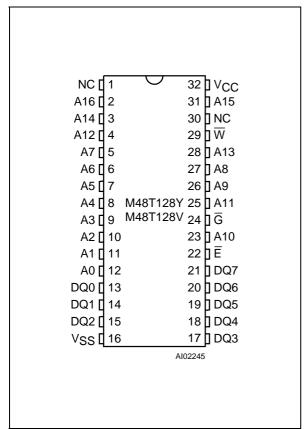


Figure 1. Logic Diagram



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DIP Pin Connections



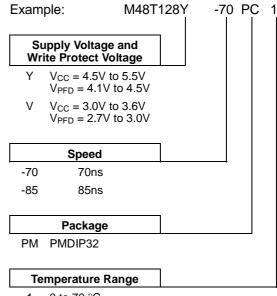
Note: NC = Not Connected.

Signal Names

A0-A16	Address Inputs
DQ0-DQ7	Data Inputs / Outputs
Ē	Chip Enable Input
G	Output Enable Input
W	Write Enable Input
Vcc	Supply Voltage
Vss	Ground

Ordering Information Scheme

For a list of available options or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.



0 to 70 °C

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